

Title (en)

SUPRACONDUCTOR STRUCTURE WITH A GLASS SUBSTRATE AND A HIGH TEMPERATURE SUPRACONDUCTOR DEPOSITED THEREON IN ADDITION TO A METHOD FOR PRODUCING SAID STRUCTURE

Title (de)

SUPRALEITERAUFBAU MIT GLASSUBSTRAT UND DARAUF ABGESCHIEDENEM HOCHTEMPERATURSUPRALEITER SOWIE VERFAHREN ZUR HERSTELLUNG DES AUFBAUS

Title (fr)

STRUCTURE SUPRACONDUCTRICE COMPORTANT UN SUBSTRAT DE VERRE SUR LEQUEL EST DEPOSE UN SUPRACONDUCTEUR HAUTE TEMPERATURE, ET PROCEDE DE PRODUCTION DE CETTE STRUCTURE

Publication

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Application

**EP 98961034 A 19981023**

Priority

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Abstract (en)

[origin: WO9922412A1] The supraconductor structure (2) comprises a substrate (3) made of a temperature resistant glass material, a buffer layer (4) deposited on said substrate, and a layer (5) deposited thereon which is made of a metal oxidic high-Tc-supraconductor-material. A glass material should be provided which has a thermal coefficient of expansion greater than 6 times  $10^{-6}$  K<sup>-1</sup> and a transformation temperature greater than 550 DEG C. In order to produce the structure, at least one depositing method is selected in which the maximum temperature is no more than 100 K higher than the transformation temperature of the glass material.

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IPC 8 full level

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